

CPH3360

Power MOSFET –30V, 303mΩ, –1.6A, Single P-Channel

This Power MOSFET is produced using ON Semiconductor's trench technology, which is specifically designed to minimize gate charge and low on resistance. This device is suitable for applications with low gate charge driving or low on resistance requirements.

Features

- High Speed Switching
- 4V drive
- Pb-Free, Halogen Free and RoHS compliance

Typical Applications

- DC/DC Converter

SPECIFICATIONS

ABSOLUTE MAXIMUM RATING at $T_a = 25^{\circ}\text{C}$ (Note 1, 2)

Parameter	Symbol	Value	Unit
Drain to Source Voltage	V_{DS}	–30	V
Gate to Source Voltage	V_{GS}	± 20	V
Drain Current (DC)	I_D	–1.6	A
Drain Current (Pulse) $PW \leq 10\mu\text{s}$, duty cycle $\leq 1\%$	I_{DP}	–6.4	A
Power Dissipation When mounted on ceramic substrate ($900\text{mm}^2 \times 0.8\text{mm}$)	P_D	0.9	W
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	–55 to +150	$^{\circ}\text{C}$

Note 1 : Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

2 : This product is designed to "ESD immunity < 200V*", so please take care when handling.

*Machine Model

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction to Ambient When mounted on ceramic substrate ($900\text{mm}^2 \times 0.8\text{mm}$)	$R_{\theta JA}$	138.8	$^{\circ}\text{C/W}$

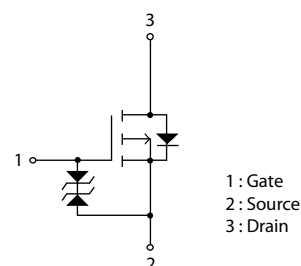


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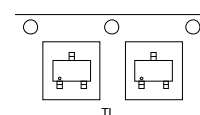
www.onsemi.com

V_{DS}	$R_{DS(on)}$ Max	I_D Max
–30V	303mΩ@ –10V	–1.6A
	532mΩ@ –4.5V	
	617mΩ@ –4V	

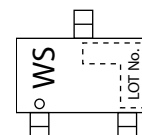
ELECTRICAL CONNECTION P-Channel



PACKING TYPE : TL



MARKING



ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

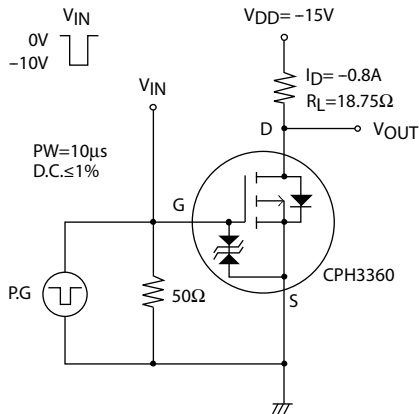
CPH3360

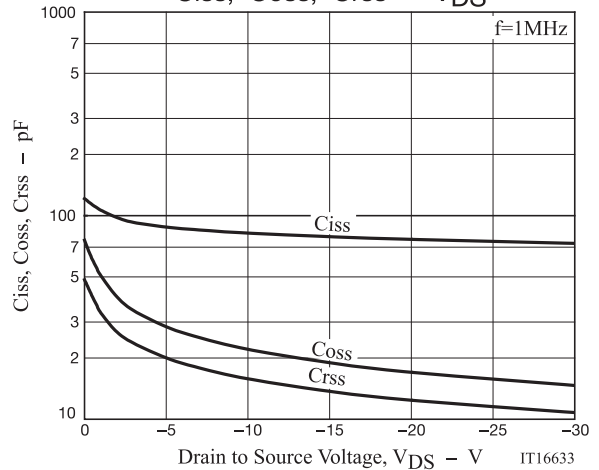
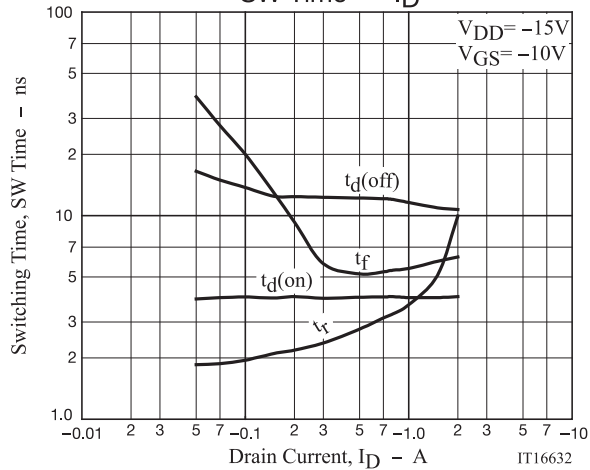
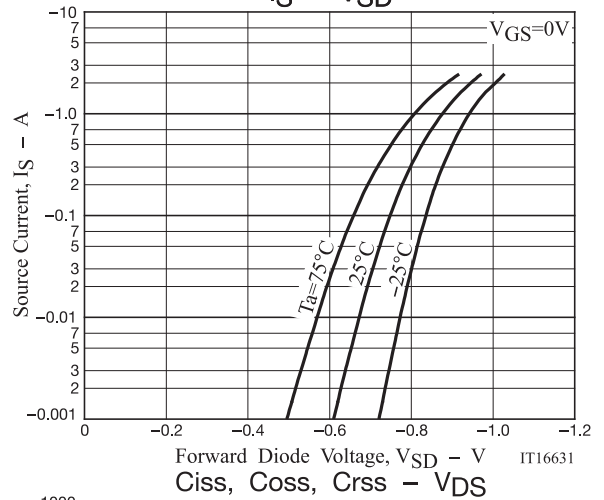
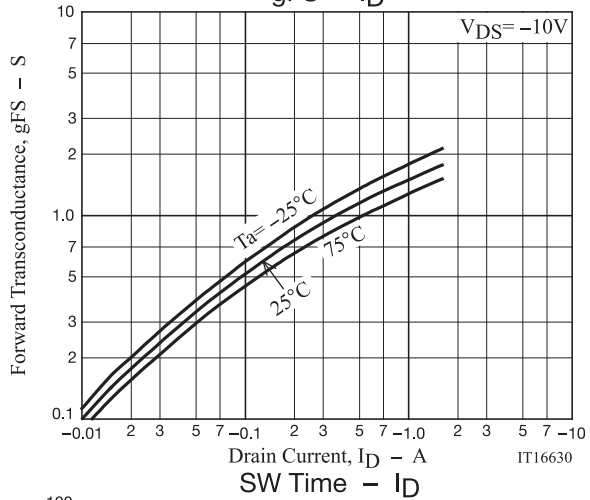
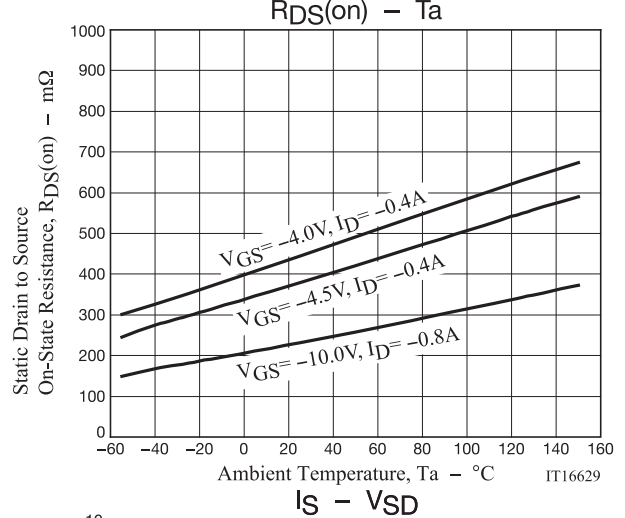
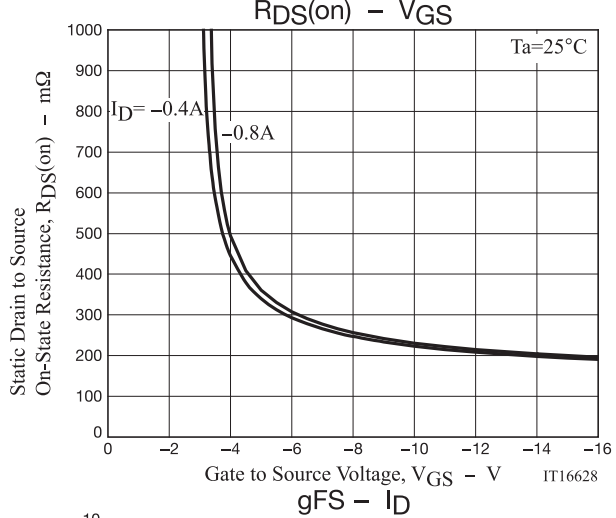
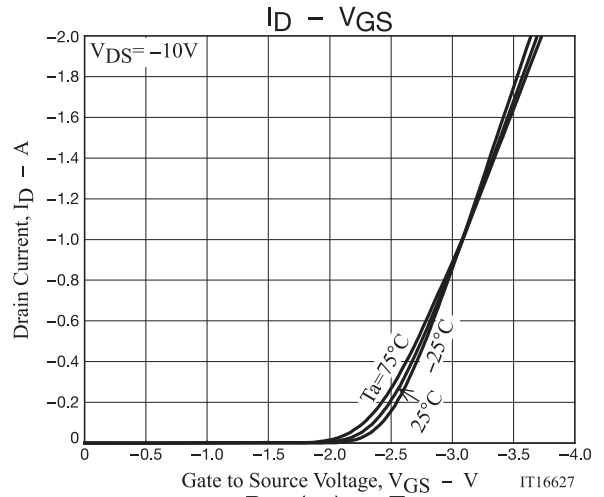
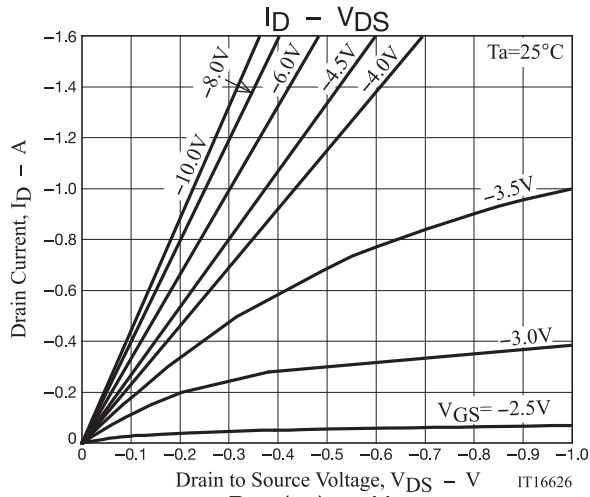
ELECTRICAL CHARACTERISTICS at Ta = 25°C (Note 3)

Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Drain to Source Breakdown Voltage	V(BR)DSS	ID=−1mA, VGS=0V	−30			V
Zero-Gate Voltage Drain Current	IDSS	VDS=−30V, VGS=0V			−1	μA
Gate to Source Leakage Current	IGSS	VGS=±16V, VDS=0V			±10	μA
Gate Threshold Voltage	VGS(th)	VDS=−10V, ID=−1mA	−1.2		−2.6	V
Forward Transconductance	gFS	VDS=−10V, ID=−0.8A		1.3		S
Static Drain to Source On-State Resistance	RDS(on)1	ID=−0.8A, VGS=−10V		233	303	mΩ
	RDS(on)2	ID=−0.4A, VGS=−4.5V		380	532	mΩ
	RDS(on)3	ID=−0.4A, VGS=−4V		441	617	mΩ
Input Capacitance	Ciss	VDS=−10V, f=1MHz		82		pF
Output Capacitance	Coss			22		pF
Reverse Transfer Capacitance	Crss			16		pF
Turn-ON Delay Time	td(on)	See specified Test Circuit		4.0		ns
Rise Time	tr			3.3		ns
Turn-OFF Delay Time	td(off)			12		ns
Fall Time	tf			5.4		ns
Total Gate Charge	Qg	VDS=−15V, VGS=−10V, ID=−1.6A		2.2		nC
Gate to Source Charge	Qgs			0.36		nC
Gate to Drain "Miller" Charge	Qgd			0.49		nC
Forward Diode Voltage	VSD	IS=−1.6A, VGS=0V		−0.9	−1.5	V

Note 3 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted.
Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Switching Time Test Circuit





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